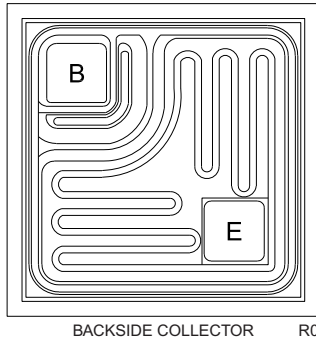


# CP327V-2N5308

## NPN - Darlington Transistor Die

### 0.3 Amp, 40 Volt

The CP327V-2N5308 die is a silicon NPN Darlington power transistor designed for high gain amplifier applications.



#### MECHANICAL SPECIFICATIONS:

Die Size	22.8 x 22.8 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Size	4.7 x 4.7 MILS
Emitter Bonding Pad Size	4.7 x 4.7 MILS
Top Side Metalization	Al-Si – 17,000Å
Back Side Metalization	Au – 9,000Å
Scribe Alley Width	1.8 mils
Wafer Diameter	5 INCHES
Gross Die Per Wafer	33,085

#### MAXIMUM RATINGS: (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V <sub>CB0</sub>	40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	12	V
Continuous Collector Current	I <sub>C</sub>	300	mA
Peak Collector Current	I <sub>CM</sub>	500	mA
Continuous Base Current	I <sub>B</sub>	100	mA
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

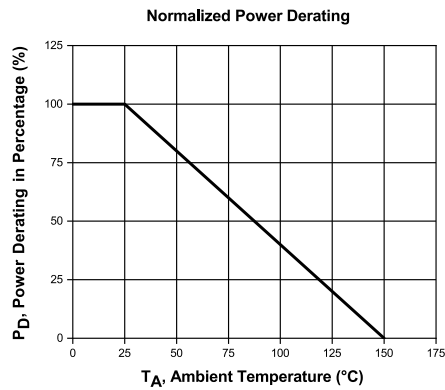
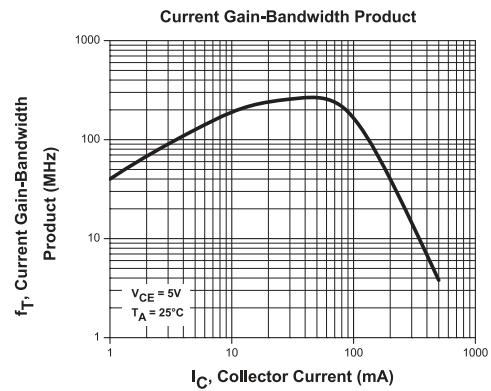
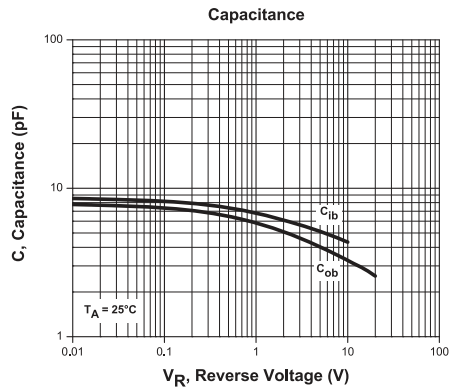
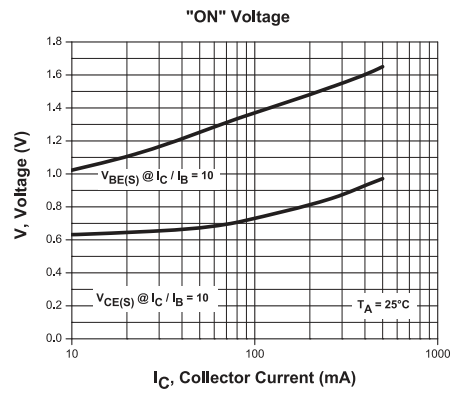
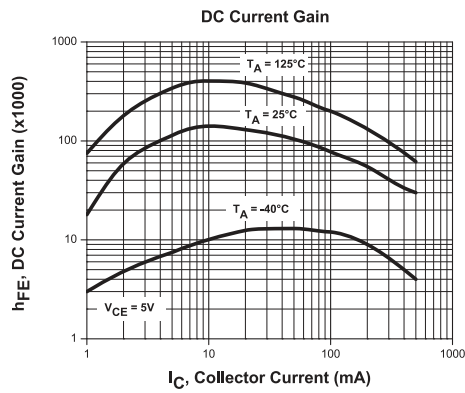
#### ELECTRICAL CHARACTERISTICS: (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>CB0</sub>	V <sub>CB</sub> =40V			100	nA
I <sub>EBO</sub>	V <sub>EB</sub> =12V			100	nA
BV <sub>CB0</sub>	I <sub>C</sub> =10μA	40			V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA	40			V
BV <sub>EBO</sub>	I <sub>E</sub> =10μA	12			V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =200mA, I <sub>B</sub> =200μA			1.4	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =200mA, I <sub>B</sub> =200μA			1.6	V
V <sub>BE(ON)</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =200mA			1.5	V
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =2.0mA	7.0K		70K	
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =100mA	20K			
h <sub>fe</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =2.0mA, f=1.0kHz	7.0K			
h <sub>fe</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =2.0mA, f=10MHz	15.6			dB
h <sub>ie</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =2.0mA, f=1.0kHz		650		kW
f <sub>T</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =2.0mA, f=10MHz	60			MHz
C <sub>cb</sub>	V <sub>CB</sub> =10V, f=1.0MHz			10	pF
C <sub>eb</sub>	V <sub>EB</sub> =0.5V, f=1.0MHz		12		pF

R0 (30-October 2019)

# CP327V-2N5308

## Typical Electrical Characteristics



## BARE DIE PACKING OPTIONS

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### BARE DIE IN TRAY (WAFFLE) PACK

**CT:** Singulated die in tray (waffle) pack.  
(example: CP211-PART NUMBER-CT)

**CM:** Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).  
(example: CP211-PART NUMBER-CM)

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### UNSAWN WAFER

**WN:** Full wafer, unsawn, 100% tested with reject die inked.  
(example: CP211-PART NUMBER-WN)

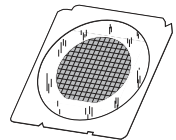
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### SAWN WAFER ON PLASTIC RING

**WR:** Full wafer, sawn and mounted on plastic ring,  
100% tested with reject die inked.  
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:  
[www.centrasemi.com/bdspecs](http://www.centrasemi.com/bdspecs)

## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

#### Corporate Headquarters & Customer Support Team

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**Worldwide Distributors:**  
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